STF10NK50Z

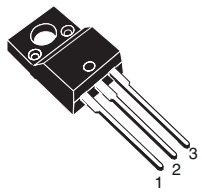
N-channel 500 V, 0.55 Ω, 9 A Zener-protected SuperMESH™ Power MOSFET in TO-220FP package

Datasheet — production data

Features

Order code	V_{DSS}	$R_{DS(on)}$ max	I_D	P_{TOT}
STF10NK50Z	500 V	< 0.7 Ω	9 A	30 W

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitance



TO-220FP

Applications

- Switching application

Description

This device is an N-channel Zener-protected Power MOSFET developed using STMicroelectronics' SuperMESH™ technology, achieved through optimization of ST's well established strip-based PowerMESH™ layout. In addition to a significant reduction in on-resistance, this device is designed to ensure a high level of dv/dt capability for the most demanding applications.

Figure 1. Internal schematic diagram

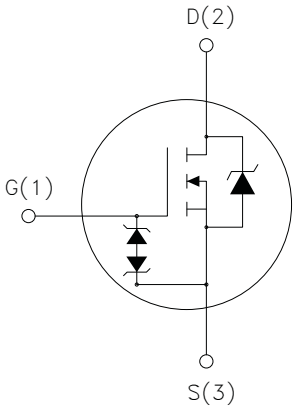


Table 1. Device summary

Order code	Marking	Package	Packaging
STF10NK50Z	F10NK50Z	TO-220FP	Tube

Contents

1 Electrical ratings 3

2 Electrical characteristics 4

2.1 Electrical characteristics (curves) 6

3 Test circuit 8

4 Package mechanical data 9

5 Revision history 12

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	500	V
V_{GS}	Gate-source voltage	± 30	V
I_D	Drain current (continuous) at T_C = 25 °C	9 (1)	A
I_D	Drain current (continuous) at T_C=100 °C	5.7 (1)	A
I_{DM}(2)	Drain current (pulsed)	36 (1)	A
P_{TOT}	Total dissipation at T_C = 25 °C	30	W
	Derating factor	0.24	W/°C
ESD	Gate-source human body model (C=100 pF, R=1.5 kΩ)	4	kV
dv/dt(3)	Peak diode recovery voltage slope	4.5	V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s;T_C=25 °C)	2500	V
T_J T_{stg}	Operating junction temperature Storage temperature	-55 to 150	°C

1. Limited by maximum junction temperature.
2. Pulse width limited by safe operating area.
3. I_{SD} ≤9 A, di/dt ≤200 A/µs,V_{DD} ≤$V_{(BR)DSS}$, T_j ≤T_{JMAX}

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case max	4.2	°C/W
$R_{thj\text{-}a}$	Thermal resistance junction-ambient max	62.5	°C/W

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by Tj max)	9	A
E_{AS}	Single pulse avalanche energy (starting Tj=25°C, I_D=I_{AR}, V_{DD}=50 V)	230	mJ

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS}= 0	500			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = 500 V V_{DS} = 500 V, T_C = 125 °C			1 50	µA µA
$V_{(BR)GSO}$	Gate-source breakdown voltage (I_D = 0)	I_{GS} = ±1 mA	±30			V
I_{GSS}	Gate body leakage current (V_{DS} = 0)	V_{GS} = ±20 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS}= V_{GS}, I_D = 100 µA	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS}= 10 V, I_D= 4.5 A		0.55	0.7	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} =25 V, f=1 MHz, V_{GS}=0	-	1219 159 40	-	pF pF pF
$C_{oss\ eq}$ (1).	Equivalent output capacitance	V_{GS}=0, V_{DS} =0 to 400 V	-	806	-	pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD}=400 V, I_D = 9 A V_{GS} =10 V See *Figure 15*	-	39.2 7.42 20.7	-	nC nC nC

1. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} inceases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	V_{DD}=250 V, I_D=4.5A, R_G=4.7Ω, V_{GS}=10V See *Figure 16*	-	19 17	-	ns ns
$t_{d(off)}$ t_f	Turn-off delay Time Fall time		-	43 15	-	ns ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current		-		9	A
I_{SDM}(1)	Source-drain current (pulsed)		-		36	A
V_{SD}(2)	Forward on voltage	I_{SD}=9 A, V_{GS}=0	-		1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD}=9 A, di/dt = 100 A/µs, V_{DD}=35 V	-	268 1.83 13.7		ns µC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD}=9 A, di/dt = 100 A/µs, V_{DD}=35 V, Tj=150 °C	-	343 2.6 15.15		ns µC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300µs, duty cycle 1.5%

Table 9. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
BV_{GSO}(1)	Gate-source breakdown voltage	Igs=±1 mA (open drain)	30	-		V

1. The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

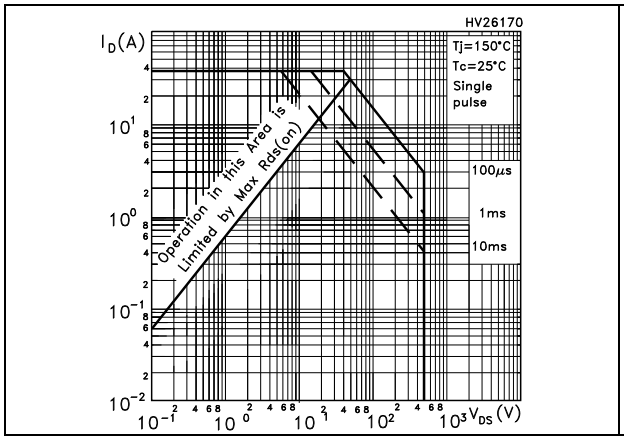


Figure 3. Thermal impedance

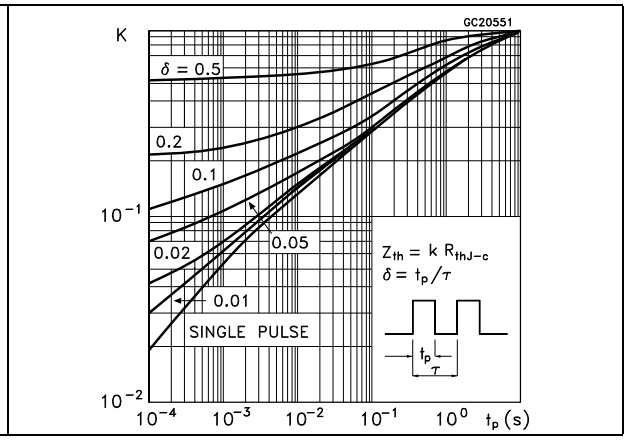


Figure 4. Output characterisics

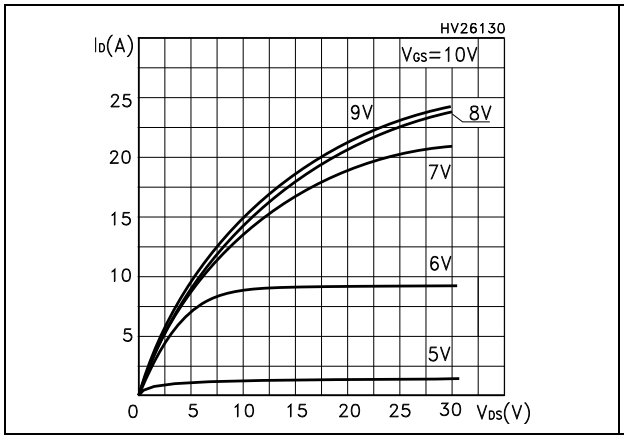


Figure 5. Transfer characteristics

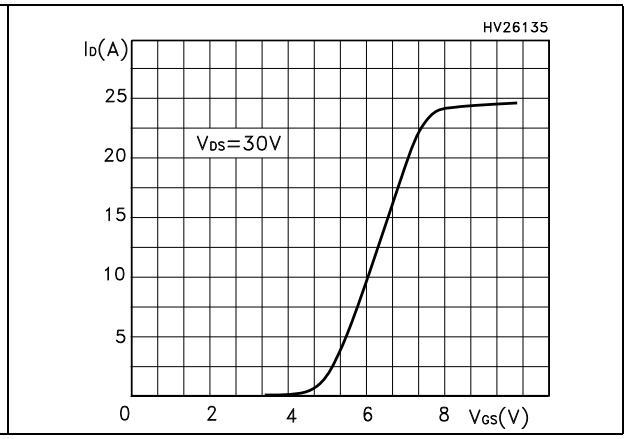


Figure 6. Normalized BV_{DSS} vs temperature

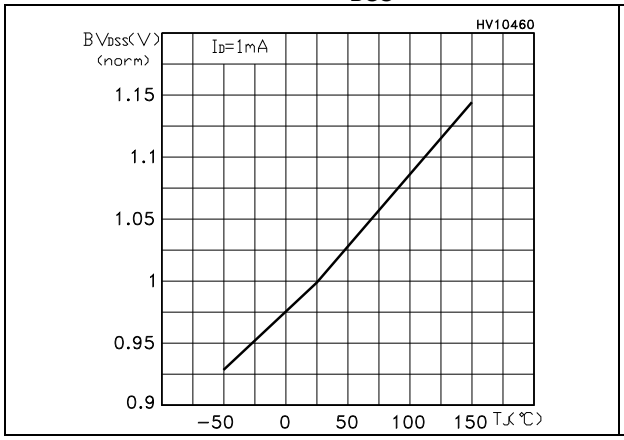


Figure 7. Static drain-source on-resistance

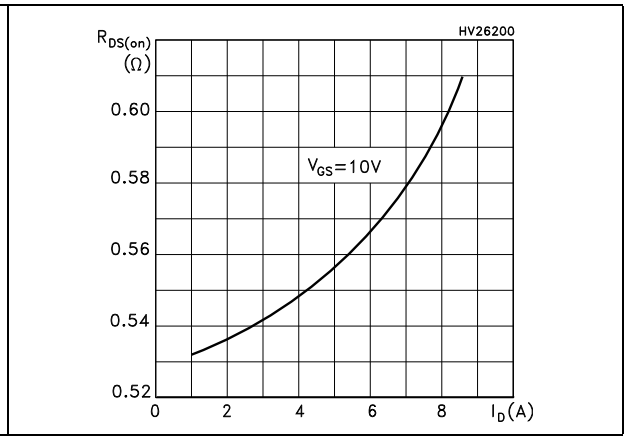


Figure 8. Gate charge vs gate-source voltage

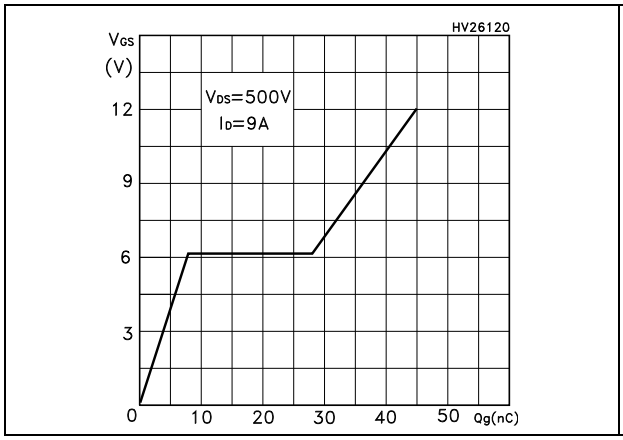


Figure 9. Capacitance variations

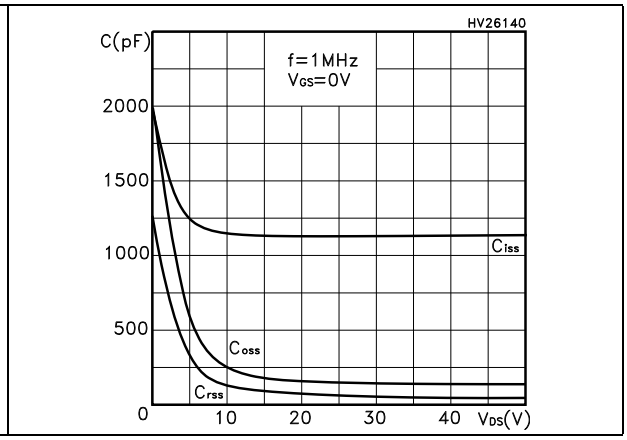


Figure 10. Normalized gate threshold voltage vs temperature

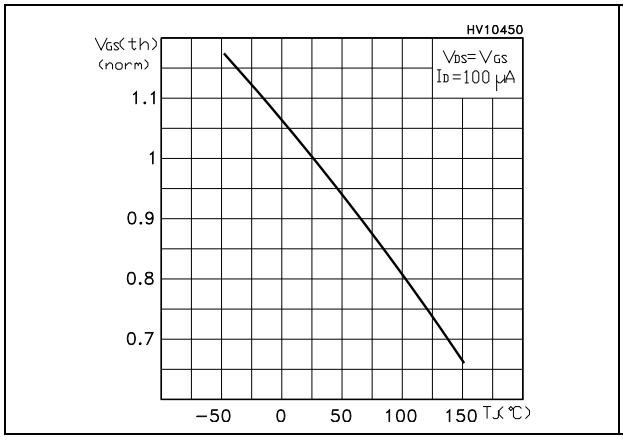


Figure 11. Normalized on resistance vs temperature

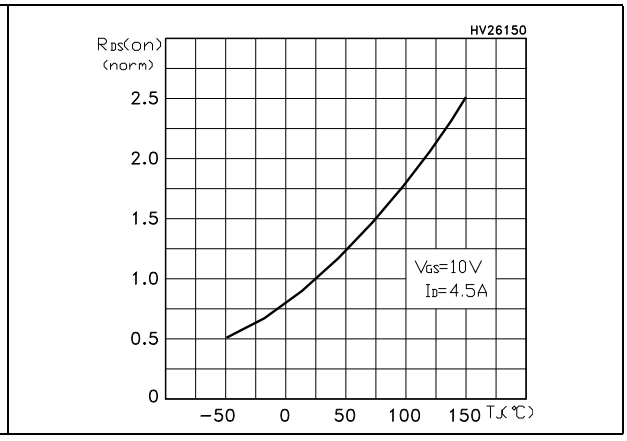


Figure 12. Source-drain diode forward characteristics

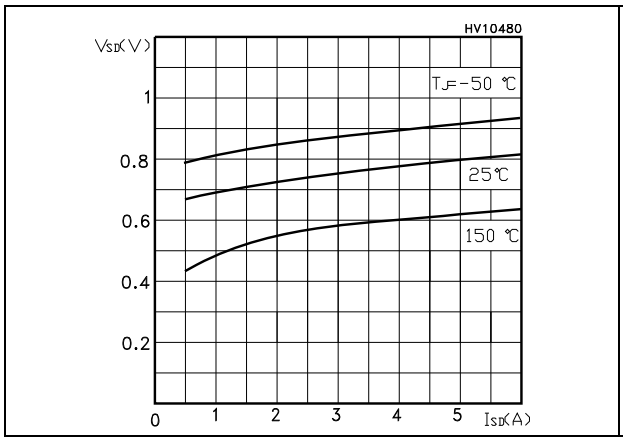
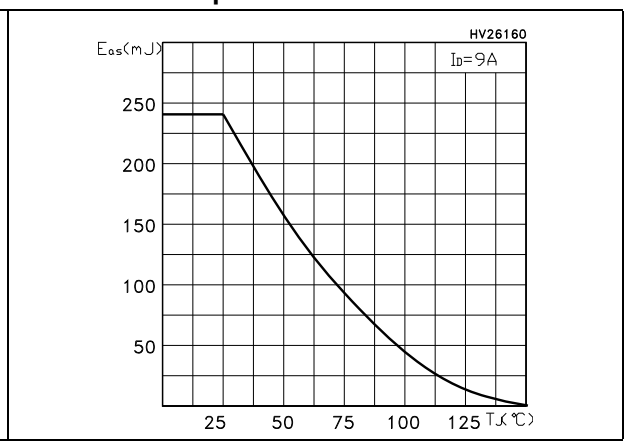


Figure 13. Maximum avalanche energy vs temperature



3 Test circuit

Figure 14. Switching times test circuit for resistive load

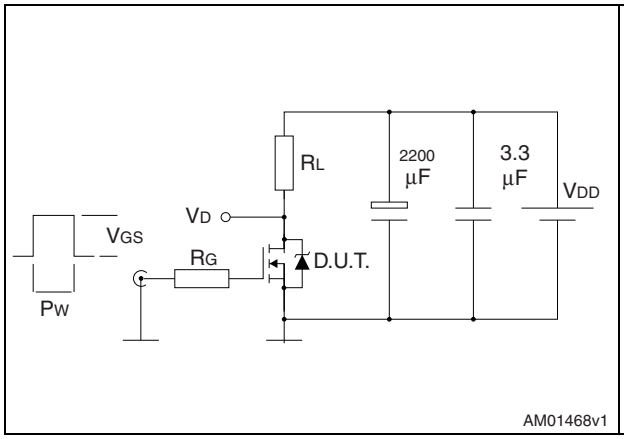


Figure 15. Gate charge test circuit

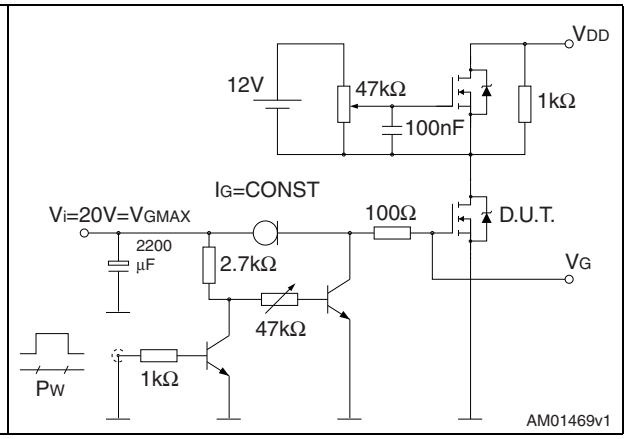


Figure 16. Test circuit for inductive load switching and diode recovery times

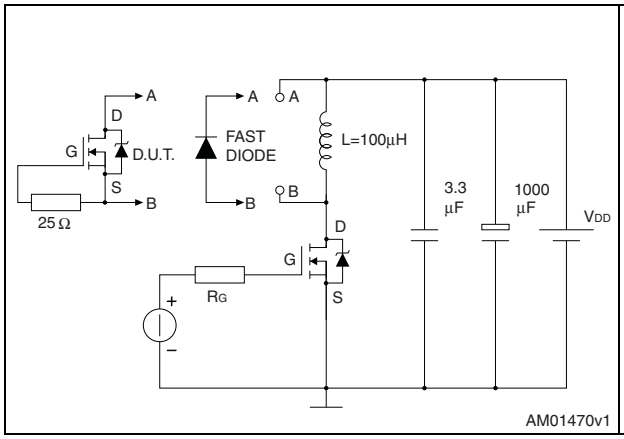


Figure 17. Unclamped inductive load test circuit

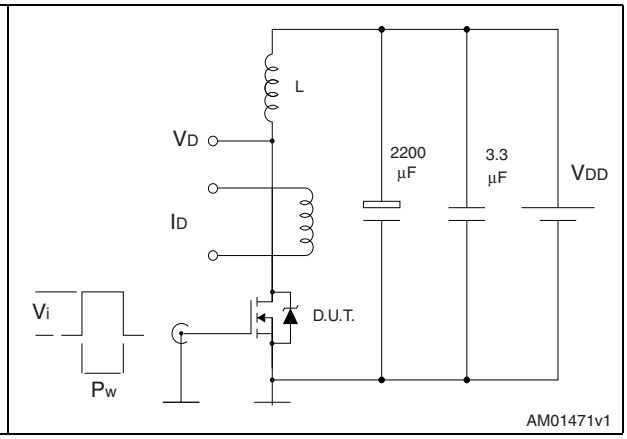


Figure 18. Unclamped inductive waveform

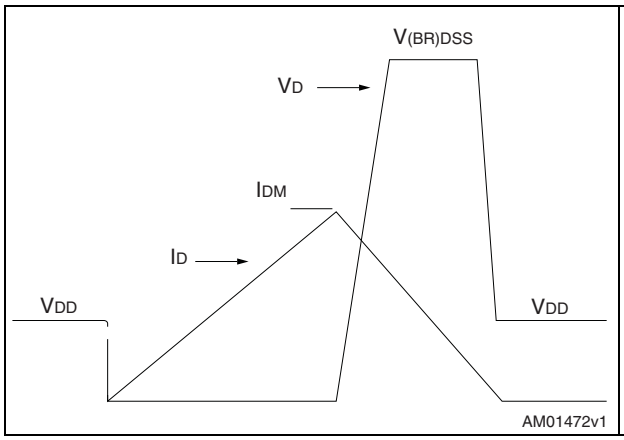
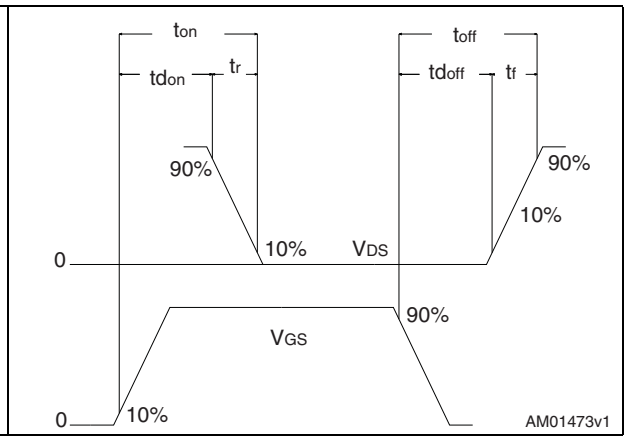


Figure 19. Switching time waveform



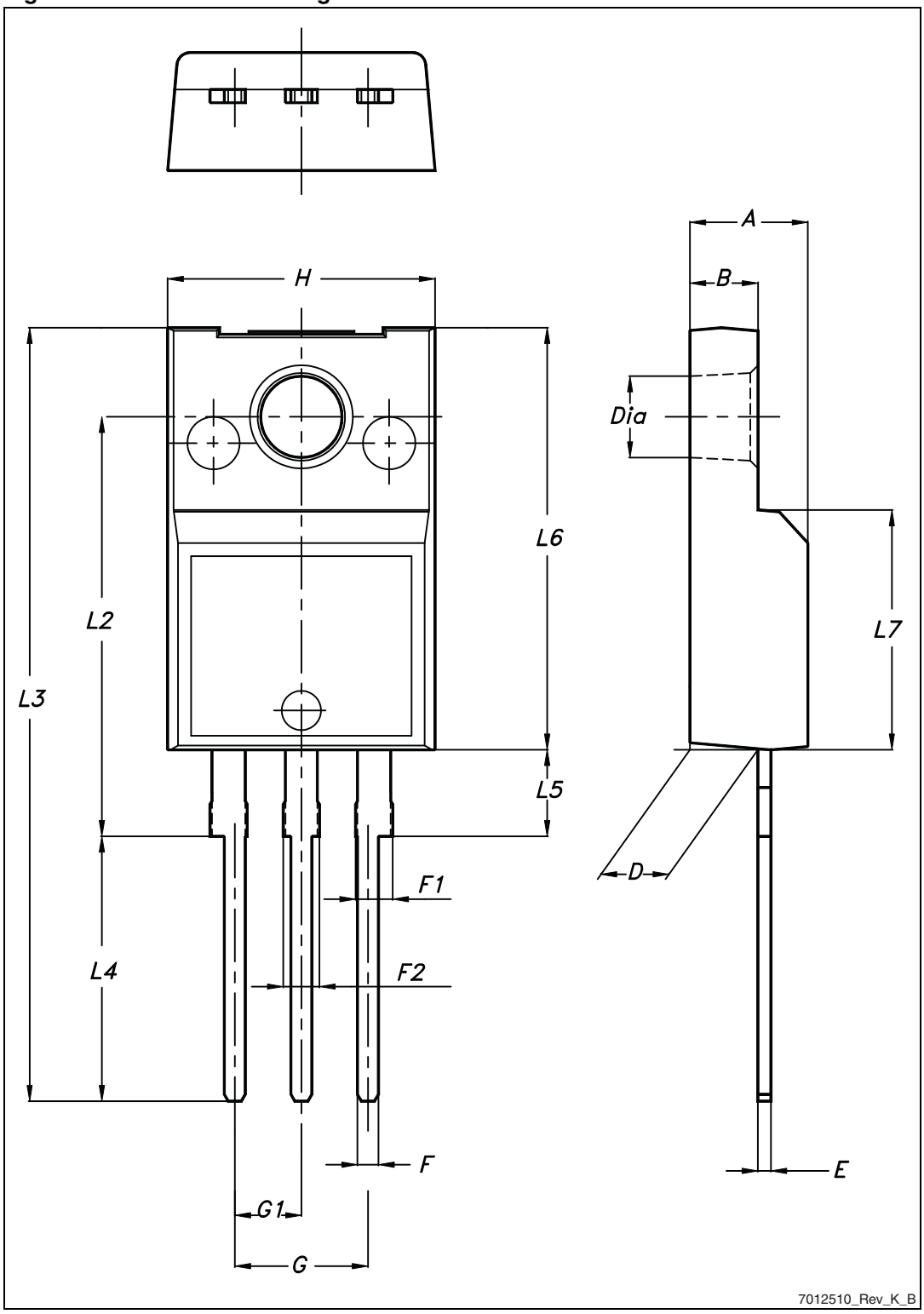
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 10. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 20. TO-220FP drawing



5 Revision history

Table 11. Document revision history

Date	Revision	Changes
28-Mar-2012	1	First release.

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